

Listing of Claims:

1 – 28. (cancelled)

29. (previously presented) A semiconductor device, comprising:

an NMOS transistor gate structure, the NMOS gate structure comprising a gate dielectric above a semiconductor body, an n-doped first metal silicide structure having a first metal component on, and in direct physical contact with, the gate dielectric; and a second metal silicide having a metal component different from the first metal component, above the n-doped first metal silicide; and

a PMOS transistor gate structure, the PMOS gate structure comprising a gate dielectric above a semiconductor body, a p-doped first metal silicide structure having the first metal component on, and in direct physical contact with, the gate dielectric; and a second metal silicide having a metal component different from the first metal component, above the p-doped first metal silicide.

30. (original) The device of claim 29, wherein the first metal silicide comprises a refractory metal.

31. (original) The device of claim 30, wherein the refractory metal is one of molybdenum, tungsten, tantalum, and titanium.

32. (original) The device of claim 29, wherein the second metal silicide comprises nickel.

33. (previously presented) The device of claim 29, further comprising a silicon layer between the first and second metal silicides in the NMOS and PMOS gate structures.

34. (canceled)

35. (previously presented) A transistor gate structure, comprising:
- a gate dielectric formed above a semiconductor body;
 - a first metal silicide on, and in direct physical contact with, the gate dielectric, the first metal silicide doped with substantially single polarity impurities and having a first metal component; and
 - a second metal silicide having a metal component different from the first metal component, above the first metal silicide.
36. (canceled)
37. (previously presented) The gate structure of claim 35, further comprising a silicon layer between the first and second metal silicides.
38. (original) The gate structure of claim 35, wherein the first metal silicide comprises a refractory metal.
39. (original) The gate structure of claim 38, wherein the refractory metal is one of molybdenum, tungsten, tantalum, and titanium.
40. (original) The gate structure of claim 38, wherein the second metal silicide comprises nickel.
41. (original) The gate structure of claim 35, wherein the second metal silicide comprises nickel.